

2018 40th Electrical Overstress/Electrostatic Discharge Symposium (EOS/ESD 2018)

**Reno, Nevada, USA
23-28 September 2018**



**IEEE Catalog Number: CFP18413-POD
ISBN: 978-1-5386-7409-3**

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IEEE Catalog Number:	CFP18413-POD
ISBN (Print-On-Demand):	978-1-5386-7409-3
ISBN (Online):	978-1-5853-7302-4
ISSN:	0739-5159

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